TMS27C256 32768 BY 8-BIT UV ERASABLE
TMS27PC256 32768 BY 8-BIT
PROGRAMMABLE READ-ONLY MEMORIES

- **Organization . . . 32768 by 8 Bits**
- **Single 5-V Power Supply**
- **Pin Compatible With Existing 256K MOS ROMs, PROMs, and EPROMs**
- **All Inputs / Outputs Fully TTL Compatible**
- **Max Access / Min Cycle Time**

  $V_{CC} \pm 10\%$

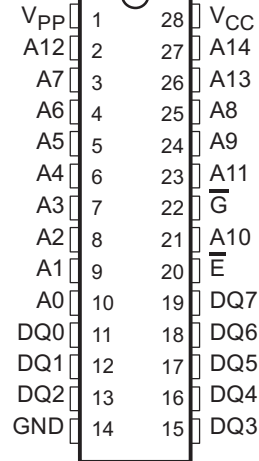 | | |
  |---|---|
  | **'27C/PC256-10** | **100 ns** |
  | **'27C/PC256-12** | **120 ns** |
  | **'27C/PC256-15** | **150 ns** |
  | **'27C/PC256-17** | **170 ns** |
  | **'27C/PC256-20** | **200 ns** |
  | **'27C/PC256-25** | **250 ns** |

- **Power Saving CMOS Technology**
- **Very High-Speed SNAP! Pulse Programming**
- **3-State Output Buffers**
- **400-mV Minimum DC Noise Immunity With Standard TTL Loads**
- **Latchup Immunity of 250 mA on All Input and Output Lines**
- **Low Power Dissipation (V_{CC} = 5.5 V)**
  - **Active . . . 165 mW Worst Case**
  - **Standby . . . 1.4 mW Worst Case (CMOS Input Levels)**
- **Temperature Range Options**
- **256K EPROM Available With MIL-STD-883C Class B High Reliability Processing (SMJ27C256)**
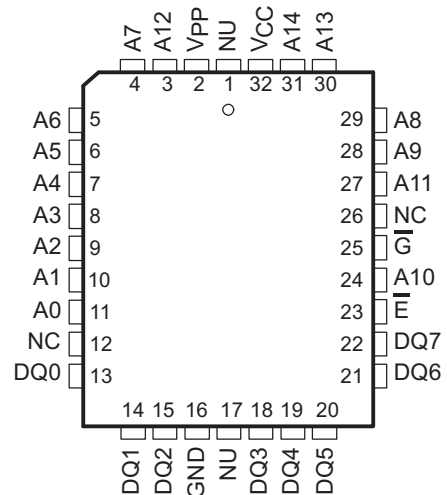
description

The TMS27C256 series are 32768 by 8-bit (262144-bit), ultraviolet (UV) light erasable, electrically programmable read-only memories (EPROMs).

The TMS27PC256 series are 32768 by 8-bit (262144-bit), one-time programmmable (OTP) electrically programmable read-only memories (PROMs).

J PACKAGE
(TOP VIEW)

V_{PP}	1	28	V_{CC}
A12	2	27	A14
A7	3	26	A13
A6	4	25	A8
A5	5	24	A9
A4	6	23	A11
A3	7	22	$\overline{G}$
A2	8	21	A10
A1	9	20	$\overline{E}$
A0	10	19	DQ7
DQ0	11	18	DQ6
DQ1	12	17	DQ5
DQ2	13	16	DQ4
GND	14	15	DQ3

FM PACKAGE
(TOP VIEW)

Top pins: A7 (4), A12 (3), V_{PP} (2), NU (1), V_{CC} (32), A14 (31), A13 (30)

Left	Pin	Pin	Right
A6	5	29	A8
A5	6	28	A9
A4	7	27	A11
A3	8	26	NC
A2	9	25	$\overline{G}$
A1	10	24	A10
A0	11	23	$\overline{E}$
NC	12	22	DQ7
DQ0	13	21	DQ6

Bottom pins: DQ1 (14), DQ2 (15), GND (16), NU (17), DQ3 (18), DQ4 (19), DQ5 (20)

PIN NOMENCLATURE	
A0–A14	Address Inputs
DQ0–DQ7	Inputs (programming)/Outputs
$\overline{E}$	Chip Enable/Powerdown
$\overline{G}$	Output Enable
GND	Ground
NC	No Internal Connection
NU	Make No External Connection
V_{CC}	5-V Power Supply
V_{PP}	13-V Power Supply †

† Only in program mode

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description (continued)

These devices are fabricated using power-saving CMOS technology for high speed and simple interface with MOS and bipolar circuits. All inputs (including program data inputs) can be driven by Series 74 TTL circuits without the use of external pull-up resistors. Each output can drive one Series 74 TTL circuit without external resistors.

The data outputs are 3-state for connecting multiple devices to a common bus. The TMS27C256 and the TMS27PC256 are pin compatible with 28-pin 256K MOS ROMs, PROMs, and EPROMs.

The TMS27C256 EPROM is offered in a dual-in-line ceramic package (J suffix) designed for insertion in mounting-hole rows on 15,2-mm (600-mil) centers. The TMS27PC256 OTP PROM is supplied in a 32-lead plastic leaded chip-carrier package using 1,25-mm (50-mil) lead spacing (FM suffix).

The TMS27C256 and TMS27PC256 are offered with two choices of temperature ranges of 0°C to 70°C (JL and FML suffixes) and – 40°C to 85°C (JE and FME suffixes). See Table 1.

All package styles conform to JEDEC standards.

Table 1. Temperature Range Suffixes

EPROM AND OTP PROM	SUFFIX FOR OPERATING FREE-AIR TEMPERATURE RANGES	
	0°C TO 70°C	– 40°C TO 85°C
TMS27C512-xxx	JL	JE
TMS27PC512-xxx	FML	FME

These EPROMs and OTP PROMs operate from a single 5-V supply (in the read mode), thus are ideal for use in microprocessor-based systems. One other 13-V supply is needed for programming . All programming signals are TTL level. These devices are programmable by the SNAP! Pulse programming algorithm. The SNAP! Pulse programming algorithm uses a V_{PP} of 13 V and a V_{CC} of 6.5 V for a nominal programming time of four seconds. For programming outside the system, existing EPROM programmers can be used. Locations can be programmed singly, in blocks, or at random.

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operation

The seven modes of operation are listed in Table 2. The read mode requires a single 5-V supply. All inputs are TTL level except for V_{PP} during programming (13 V for SNAP! Pulse), and 12 V on A9 for the signature mode.

Table 2. Operation Modes

FUNCTION	MODE†							
	READ	OUTPUT DISABLE	STANDBY	PROGRAMMING	VERIFY	PROGRAM INHIBIT	SIGNATURE MODE	
$\overline{E}$	V_{IL}	V_{IL}	V_{IH}	V_{IL}	V_{IH}	V_{IH}	V_{IL}	
$\overline{G}$	V_{IL}	V_{IH}	X	V_{IH}	V_{IL}	X	V_{IL}	
V_{PP}	V_{CC}	V_{CC}	V_{CC}	V_{PP}	V_{PP}	V_{PP}	V_{CC}	
V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	
A9	X	X	X	X	X	X	V_H‡	V_H‡
A0	X	X	X	X	X	X	V_{IL}	V_{IH}
DQ0–DQ7	Data Out	Hi-Z	Hi-Z	Data In	Data Out	Hi-Z	CODE	
							MFG	DEVICE
							97	04

† X can be V_{IL} or V_{IH}.
‡ V_H = 12 V ± 0.5 V.

read/output disable

When the outputs of two or more TMS27C256s or TMS27PC256s are connected in parallel on the same bus, the output of any particular device in the circuit can be read with no interference from the competing outputs of the other devices. To read the output of a single device, a low-level signal is applied to the $\overline{E}$ and $\overline{G}$ pins. All other devices in the circuit should have their outputs disabled by applying a high-level signal to one of these pins. Output data is accessed at pins DQ0 through DQ7.

latchup immunity

Latchup immunity on the TMS27C256 and TMS27PC256 is a minimum of 250 mA on all inputs and outputs. This feature provides latchup immunity beyond any potential transients at the P.C. board level when the devices are interfaced to industry-standard TTL or MOS logic devices. Input-output layout approach controls latchup without compromising performance or packing density.

power down

Active I_{CC} supply current can be reduced from 30 mA to 500 μA (TTL-level inputs) or 250 μA (CMOS-level inputs) by applying a high TTL or CMOS signal to the $\overline{E}$ pin. In this mode all outputs are in the high-impedance state.

erasure (TMS27C256)

Before programming, the TMS27C256 EPROM is erased by exposing the chip through the transparent lid to a high intensity ultraviolet light (wavelength 2537 Å). EPROM erasure before programming is necessary to assure that all bits are in the logic high state. Logic lows are programmed into the desired locations. A programmed logic low can be erased only by ultraviolet light. The recommended minimum exposure dose (UV intensity × exposure time) is 15-W•s/cm^2. A typical 12-mW/cm^2, filterless UV lamp erases the device in 21 minutes. The lamp should be located about 2.5 cm above the chip during erasure. It should be noted that normal ambient light contains the correct wavelength for erasure. Therefore, when using the TMS27C256, the window should be covered with an opaque label.

initializing (TMS27PC256)

The one-time programmable TMS27PC256 PROM is provided with all bits in the logic high state, then logic lows are programmed into the desired locations. Logic lows programmed into an OTP PROM cannot be erased.

SNAP! Pulse programming

The 256K EPROM and OTP PROM are programmed using the TI SNAP! Pulse programming algorithm illustrated by the flowchart in Figure 1, which programs in a nominal time of four seconds. Actual programming time varies as a function of the programmer used.

Data is presented in parallel (eight bits) on pins DQ0 to DQ7. Once addresses and data are stable, $\overline{E}$ is pulsed.

The SNAP! Pulse programming algorithm uses initial pulses of 100 microseconds (μs) followed by a byte verification to determine when the addressed byte has been successfully programmed. Up to 10 (ten) 100-μs pulses per byte are provided before a failure is recognized.

The programming mode is achieved when V_{PP} = 13 V, V_{CC} = 6.5 V, $\overline{G}$ = V_{IH}, and $\overline{E}$ = V_{IL}. More than one device can be programmed when the devices are connected in parallel. Locations can be programmed in any order. When the SNAP! Pulse programming routine is complete, all bits are verified with V_{CC} = V_{PP} = 5 V.

program inhibit

Programming can be inhibited by maintaining a high level input on the $\overline{E}$ pin.

program verify

Programmed bits can be verified with V_{PP} = 13 V when $\overline{G}$ = V_{IL} and $\overline{E}$ = V_{IH}.

signature mode

The signature mode provides access to a binary code identifying the manufacturer and type. This mode is activated when A9 is forced to 12 V. Two identifier bytes are accessed by toggling A0. All other addresses must be held low. The signature code for these devices is 9704. A0 selects the manufacturer's code 97 (Hex), and A0 high selects the device code 04, as shown in Table 3.

Table 3. Signature Mode

IDENTIFIER†	PINS									
	A0	DQ7	DQ6	DQ5	DQ4	DQ3	DQ2	DQ1	DQ0	HEX
MANUFACTURER CODE	V_{IL}	1	0	0	1	0	1	1	1	97
DEVICE CODE	V_{IH}	0	0	0	0	0	1	0	0	04

† $\overline{E}$ = $\overline{G}$ = V_{IL}, A9 = V_H, A1−A8 = V_{IL}, A10−A15 = V_{IL}, V_{PP} = V_{CC}, $\overline{PGM}$ = V_{IH} or V_{IL}.

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Start

Address = First Location

V_{CC} = 6.5 V, V_{PP} = 13 V

Program One Pulse = t_w = 100 μs

Increment Address

Last Address? — No

Yes

Address = First Location

X = 0

Program One Pulse = t_w = 100 μs

Increment Address

Verify One Byte — Fail

X = X + 1

X = 10? — No / Yes

Pass

Last Address? — No

Yes

V_{CC} = V_{PP} = 5 V ±10%

Device Failed

Compare All Bytes To Original Data — Fail

Pass

Device Passed

Program Mode

Interactive Mode

Final Verification
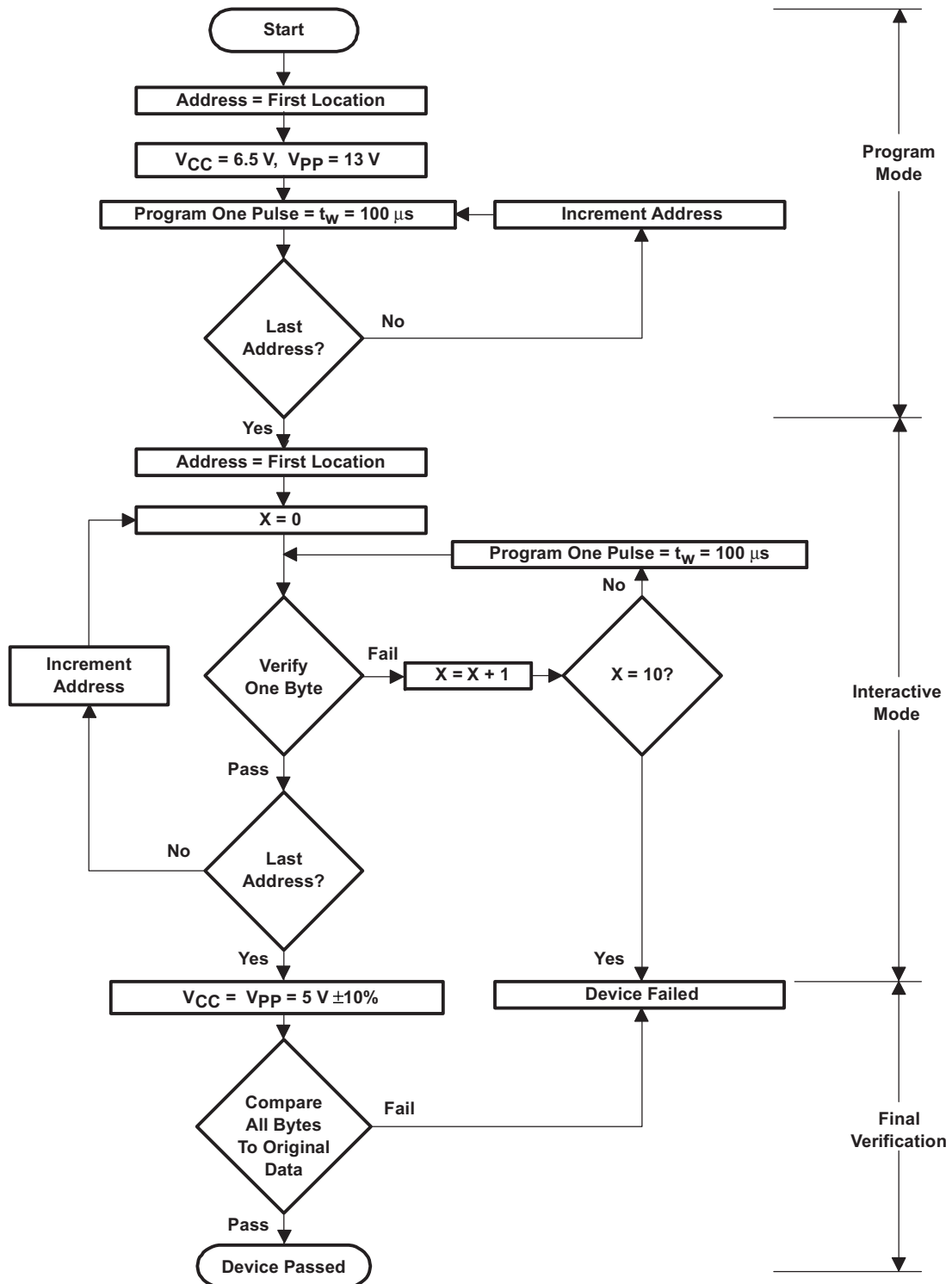
Figure 1. SNAP! Pulse Programming Flowchart

logic symbol[†]

[†] These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
  Pin numbers shown are for J package.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[‡]

Supply voltage range, V_{CC} (see Note 1) : . . . . −0.6 V to 7 V
Supply voltage range, V_{PP} : . . . . −0.6 V to 14 V
Input voltage range (see Note 1): All inputs except A9 : . . . . −0.6 V to V_{CC} + 1 V
                                                 A9 : . . . . −0.6 V to 13.5 V
Output voltage range (see Note 1) : . . . . −0.6 V to V_{CC} + 1 V
Operating free-air temperature range ('27C256-_ _JL, '27PC256-_ _FML) T_A : . . . . 0°C to 70°C
Operating free-air temperature range ('27C5256-_ _JE, '27PC256-_ _FME) T_A : . . . . −40°C to 85°C
Storage temperature range, T_{stg} : . . . . −65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and
  functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not
  implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTE 1: All voltage values are with respect to GND.

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recommended operating conditions

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	Read mode (see Note 2)	4.5	5	5.5	V
		SNAP! Pulse programming algorithm	6.25	6.5	6.75	
V_{PP}	Supply voltage	Read mode	$V_{CC}-0.6$		$V_{CC}+0.6$	V
		SNAP! Pulse programming algorithm	12.75	13	13.25	
V_{IH}	High-level dc input voltage	TTL	2		$V_{CC}+1$	V
		CMOS	$V_{CC}-0.2$		$V_{CC}+1$	
V_{IL}	Low-level dc input voltage	TTL	-0.5		0.8	V
		CMOS	-0.5		0.2	
T_A	Operating free-air temperature	'27C256-_ _JL '27PC256-_ _FML	0		70	°C
T_A	Operating free-air temperature	'27C256-_ _JE '27PC256-_ _FME	-40		85	°C

NOTE 2: V_{CC} must be applied before or at the same time as V_{PP}. V_{CC} must be removed after or at the same time as V_{PP}. The device must not be inserted into or removed from the board when V_{PP} or V_{CC} is applied.

electrical characteristics over recommended ranges of operating conditions

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OH}	High-level dc output voltage	$I_{OH} = -2.5$ mA	3.5			V
		$I_{OH} = -20$ μA	$V_{CC}-0.1$			
V_{OL}	Low-level dc output voltage	$I_{OL} = 2.1$ mA			0.4	V
		$I_{OL} = 20$ μA			0.1	
I_I	Input current (leakage)	$V_I = 0$ V to 5.5 V			±1	μA
I_O	Output current (leakage)	$V_O = 0$ V to V_{CC}			±1	μA
I_{PP1}	V_{PP} supply current	$V_{PP} = V_{CC} = 5.5$ V		1	10	μA
I_{PP2}	V_{PP} supply current (during program pulse)	$V_{PP} = 13$ V		35	50	mA
I_{CC1}	V_{CC} supply current (standby)	TTL-input level	$V_{CC} = 5.5$ V, $\overline{E} = V_{IH}$		250	500	μA
		CMOS-input level	$V_{CC} = 5.5$ V, $\overline{E} = V_{CC}$		100	250	
I_{CC2}	V_{CC} supply current (active)		$V_{CC} = 5.5$ V, $\overline{E} = V_{IL}$, t_{cycle} = minimum cycle time, outputs open		15	30	mA

capacitance over recommended ranges of supply voltage and operating free-air temperature, f = 1 MHz†

PARAMETER		TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
C_i	Input capacitance	$V_I = 0$, f = 1 MHz		6	10	pF
C_O	Output capacitance	$V_O = 0$, f = 1 MHz		10	14	pF

† Capacitance measurements are made on a sample basis only.
‡ Typical values are at $T_A = 25°C$ and nominal voltages.

switching characteristics over recommended range of operating conditions

PARAMETER		TEST CONDITIONS (SEE NOTES 3 AND 4)	'27C256-10 '27PC256-10		'27C256-12 '27PC256-12		'27C256-15 '27PC256-15		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
$t_{a(A)}$	Access time from address	C_L = 100 pF, 1 Series 74 TTL Load, Input $t_r \leq$ 20 ns, Input $t_f \leq$ 20 ns		100		120		150	ns
$t_{a(E)}$	Access time from chip enable			100		120		150	ns
$t_{en(G)}$	Output enable time from $\overline{G}$			55		55		75	ns
t_{dis}	Output disable time from $\overline{G}$ or $\overline{E}$, whichever occurs first†		0	45	0	45	0	60	ns
$t_{v(A)}$	Output data valid time after change of address, $\overline{E}$, or $\overline{G}$, whichever occurs first†		0		0		0		ns

PARAMETER		TEST CONDITIONS (SEE NOTES 3 AND 4)	'27C256-17 '27PC256-17		'27C256-20 '27PC256-20		'27C256-25 '27PC256-25		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
$t_{a(A)}$	Access time from address	C_L = 100 pF, 1 Series 74 TTL Load, Input $t_r \leq$ 20 ns, Input $t_f \leq$ 20 ns		170		200		250	ns
$t_{a(E)}$	Access time from chip enable			170		200		250	ns
$t_{en(G)}$	Output enable time from $\overline{G}$			75		75		100	ns
t_{dis}	Output disable time from $\overline{G}$ or $\overline{E}$, whichever occurs first†		0	60	0	60	0	60	ns
$t_{v(A)}$	Output data valid time after change of address, $\overline{E}$, or $\overline{G}$, whichever occurs first†		0		0		0		ns

† Value calculated from 0.5 V delta to measured level. This parameter is only sampled and not 100% tested.
NOTES: 3. For all switching characteristics the input pulse levels are 0.4 V to 2.4 V. Timing measurements are made at 2 V for logic high and 0.8 V for logic low) (see Figure 2).
4. Common test conditions apply for the t_{dis} except during programming.

switching characteristics for programming: V_{CC} = 6.50 V and V_{PP} = 13 V (SNAP! Pulse), T_A = 25°C (see Note 3)

PARAMETER		MIN	MAX	UNIT
$t_{dis(G)}$	Output disable time from $\overline{G}$	0	130	ns
$t_{en(G)}$	Output enable time from $\overline{G}$		150	ns

NOTE 3: For all switching characteristics, the input pulse levels are 0.4 V to 2.4 V. Timing measurements are made at 2 V for logic high and 0.8 V for logic low).
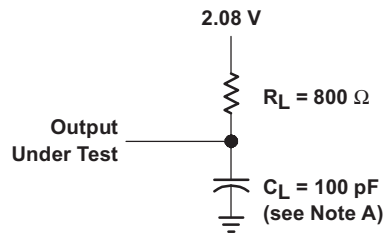
timing requirements for programming

		MIN	NOM	MAX	UNIT
$t_{h(A)}$	Hold time, address	0			µs
$t_{h(D)}$	Hold time, data	2			µs
$t_{w(IPGM)}$	Pulse duration, initial program	95	100	105	µs
$t_{su(A)}$	Setup time, address	2			µs
$t_{su(G)}$	Setup time, $\overline{G}$	2			µs
$t_{su(E)}$	Setup time, $\overline{E}$	2			µs
$t_{su(D)}$	Setup time, data	2			µs
$t_{su(VPP)}$	Setup time, V_{PP}	2			µs
$t_{su(VCC)}$	Setup time, V_{CC}	2			µs

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PARAMETER MEASUREMENT INFORMATION

2.08 V

R_L = 800 Ω

**Output
Under Test**

C_L = 100 pF
(see Note A)

NOTE A: C_L includes probe and fixture capacitance.

ac testing input/output wave forms

2.4 V

2 V   2 V
0.8 V   0.8 V

0.4 V
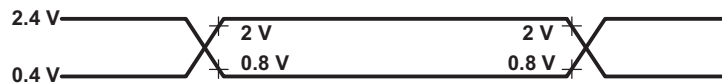
AC testing inputs are driven at 2.4 V for logic high and 0.4 V for logic low. Timing measurements are made at 2 V for logic high and 0.8 V for logic low for both inputs and outputs.
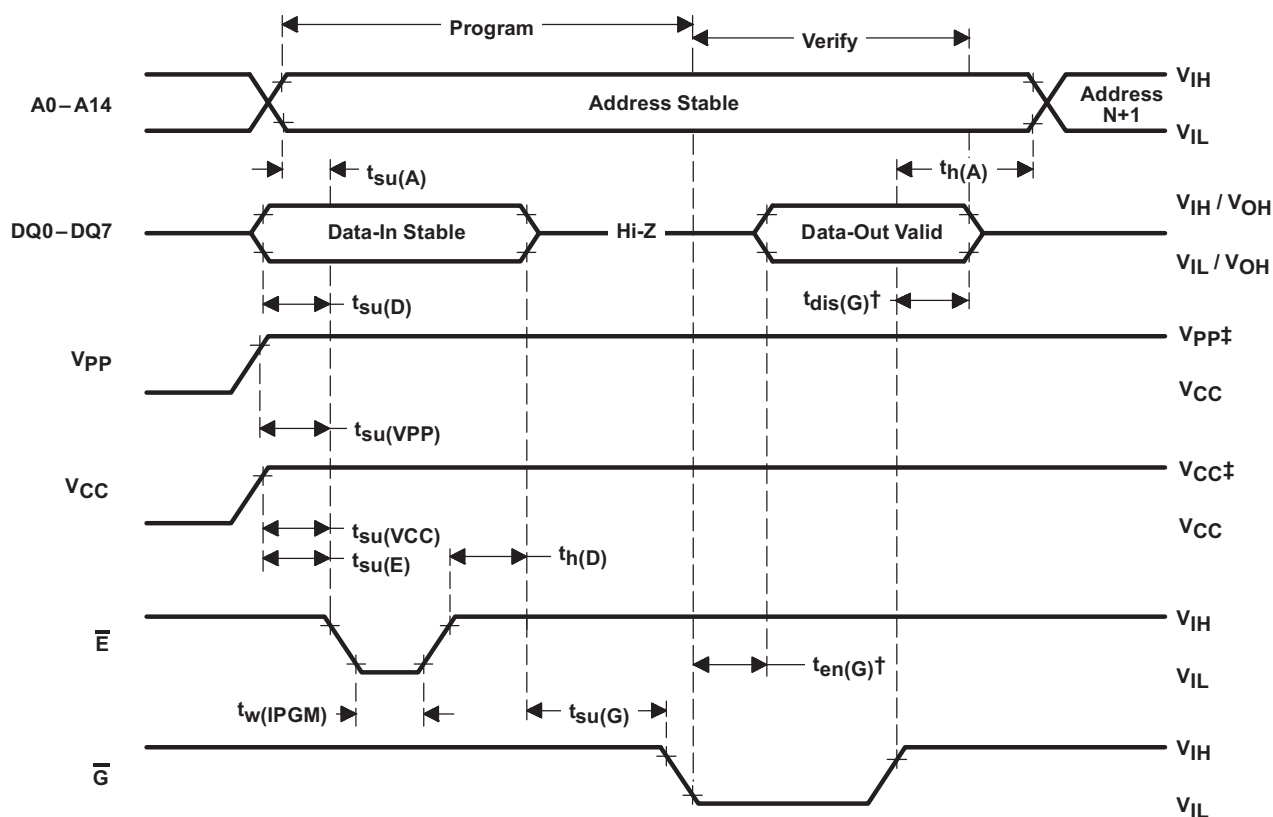
Figure 2. AC Testing Output Load Circuit

A0–A14 V_{IH}
Addresses Valid
V_{IL}

$\overline{E}$ V_{IH}
V_{IL}

$t_{a(E)}$

$\overline{G}$ V_{IH}
V_{IL}

$t_{en(G)}$ t_{dis}

$t_{a(A)}$ $t_{v(A)}$

V_{OH}
DQ0–DQ7   Hi-Z   **Output Valid**   Hi-Z
V_{OL}
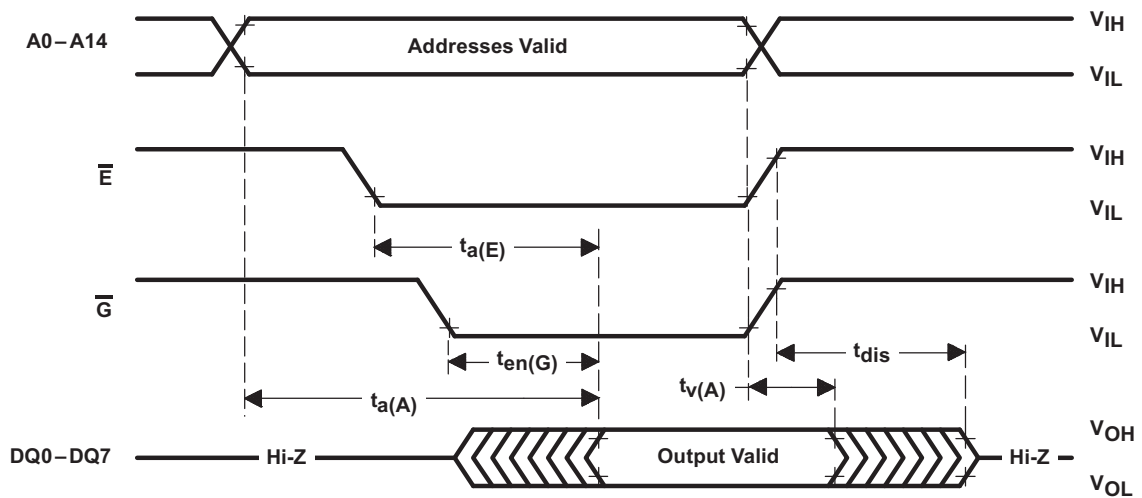
Figure 3. Read-Cycle Timing

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PARAMETER MEASUREMENT INFORMATION

† $t_{dis(G)}$ and $t_{en(G)}$ are characteristics of the device but must be accommodated by the programmer
‡ 13-V V_{PP} and 6.5-V V_{CC} for SNAP! Pulse programming

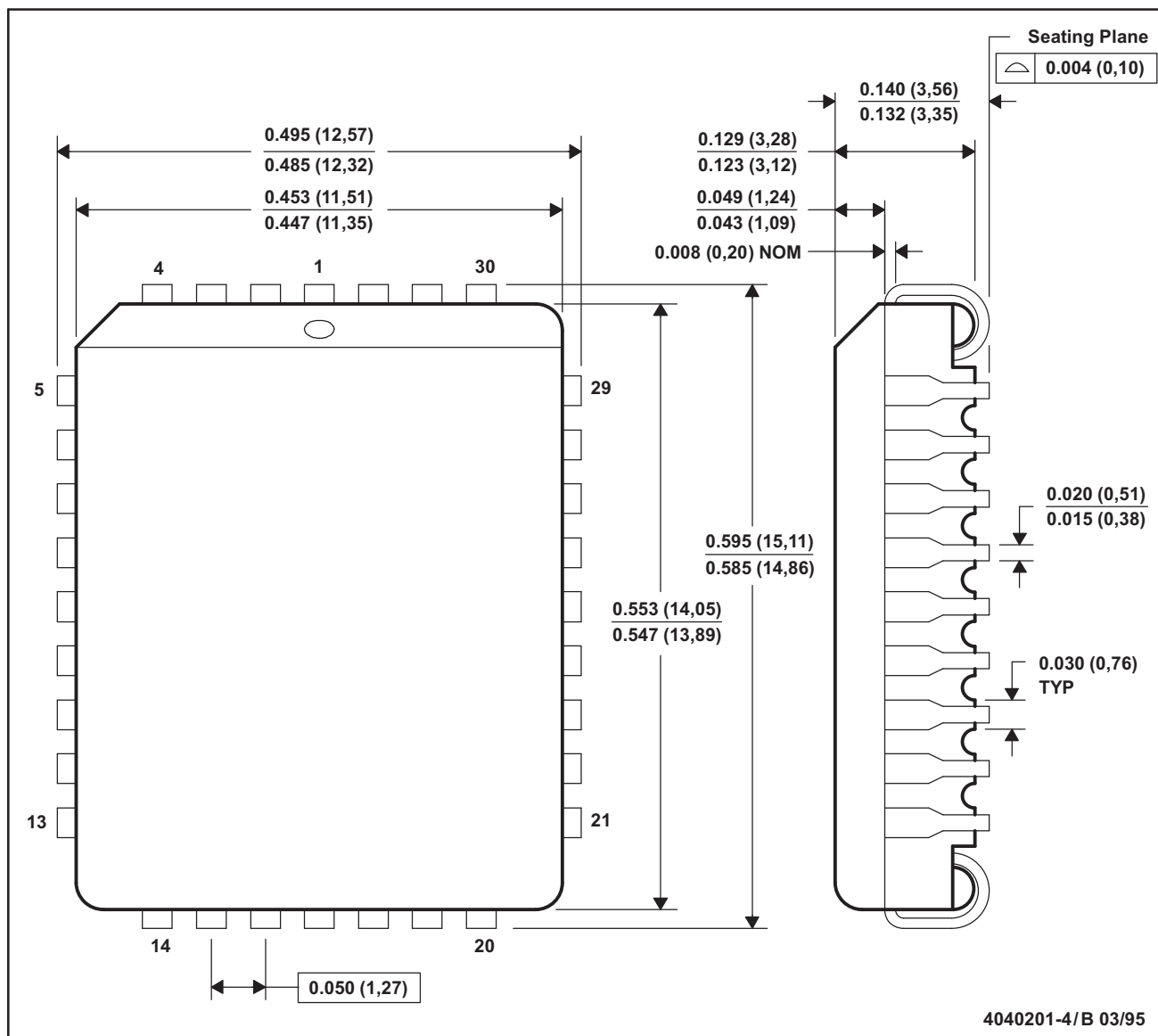**Figure 4. Program-Cycle Timing (SNAP! Pulse Programming)**

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FM (R-PQCC-J32)   **PLASTIC J-LEADED CHIP CARRIER**

4040201-4 / B 03/95

NOTES: A. All linear dimensions are in inches (millimeters).
        B. This drawing is subject to change without notice.
        C. Falls within JEDEC MS-016

J (R-CDIP-T)**   CERAMIC SIDE-BRAZE DUAL-IN-LINE PACKAGE

24 PIN SHOWN

| | PINS** | 24 | | 28 | | 32 | | 40 | |
DIM		NARR	WIDE	NARR	WIDE	NARR	WIDE	NARR	WIDE
A	MAX	0.624(15,85)	0.624(15,85)	0.624(15,85)	0.624(15,85)	0.624(15,85)	0.624(15,85)	0.624(15,85)	0.624(15,85)
	MIN	0.590(14,99)	0.590(14,99)	0.590(14,99)	0.590(14,99)	0.590(14,99)	0.590(14,99)	0.590(14,99)	0.590(14,99)
B	MAX	1.265(32,13)	1.265(32,13)	1.465(37,21)	1.465(37,21)	1.668(42,37)	1.668(42,37)	2.068(52,53)	2.068(52,53)
	MIN	1.235(31,37)	1.235(31,37)	1.435(36,45)	1.435(36,45)	1.632(41,45)	1.632(41,45)	2.032(51,61)	2.032(51,61)
C	MAX	0.541(13,74)	0.598(15,19)	0.541(13,74)	0.598(15,19)	0.541(13,74)	0.598(15,19)	0.541(13,74)	0.598(15,19)
	MIN	0.514(13,06)	0.571(14,50)	0.514(13,06)	0.571(14,50)	0.514(13,06)	0.571(14,50)	0.514(13,06)	0.571(14,50)

4040084 / B 04/95

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.

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